

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (currently amended): A method for the fabrication of a semiconductor light-emitting device, comprising the steps of:

stacking at least a first conductive type semiconductor layer, an active layer and a second conductive type semiconductor layer on a substrate to form a wafer;

forming on a side of growth surfaces of the semiconductor layers first trenches exposing the first conductive type semiconductor layer;

forming second trenches reaching the substrate from above the first trenches by the use of a laser beam;

forming third trenches from the substrate at positions corresponding to the second trenches by the use of a laser beam;

using a dicing blade to correct a shape of the third trenches; and

dividing the wafer into chips.

2. (original): A method according to claim 1, wherein the third trenches have a greater width than the second trenches.

3. (currently amended): A method according to claim 1 ~~or claim 2~~, wherein the third trenches have a greater width than the first trenches.

4. - 5. (canceled)

6. (currently amended): A method according to claim 1~~any one of claims 1 to 4~~, wherein the third trenches are formed by radiating a laser beam two times or more.

7. (currently amended): A method according to claim 1~~any one of claims 1 to 6~~, wherein the substrate is lapped, ground or polished till a thickness thereof reaches 100  $\mu\text{m}$  or less inclusive of an epitaxial layer prior to the formation of the third trenches.

8. (currently amended): A method according to claim 1~~any one of claims 1 to 7~~, wherein the first conductive type semiconductor layer is an n-type semiconductor layer and the second conductive type semiconductor layer is a p-type semiconductor layer.

9. (currently amended): A method according to claim 1~~any one of claims 1 to 9~~, wherein the substrate is a sapphire substrate.

10. (currently amended): A method according to claim 1~~any one of claims 1 to 9~~, wherein the semiconductor light-emitting device is a nitride-based semiconductor light-emitting device.

11. (currently amended): A method according to claim 1~~any one of claims 1 to 10~~, wherein the semiconductor light-emitting device is a gallium nitride-based semiconductor light-emitting device.

12. (currently amended): A semiconductor light-emitting device produced by using the method for the fabrication of the semiconductor light-emitting device according to claim 1~~any one of claims 1 to 11~~.